



# E4D20120A

## E-Series Automotive 4th Generation 1200 V, 20 A Silicon Carbide Schottky Diode

### Description

With the performance advantages of a Silicon Carbide (SiC) Schottky Barrier diode, power electronics systems can expect to meet higher efficiency standards than Si-based solutions, while also reaching higher frequencies and power densities. SiC diodes can be easily paralleled to meet various application demands, without concern of thermal runaway. In combination with the reduced cooling requirements and improved thermal performance of SiC products, SiC diodes are able to provide lower overall system costs in a variety of diverse applications.



Package Types: TO-220-2  
Marking: E4D20120A

### Features

- Low Forward Voltage ( $V_F$ ) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior
- Automotive Qualified (AEC Q101) and PPAP Capable

### Applications

- Industrial Switched Mode Power Supplies
- Uninterruptible & AUX Power Supplies
- Boost for PFC & DC-DC Stages
- Solar Inverters

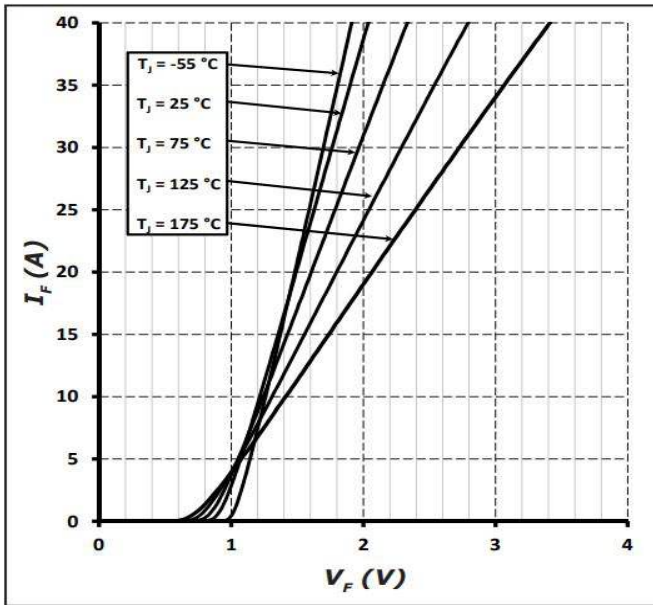
### Maximum Ratings ( $T_C = 25^\circ\text{C}$ Unless Otherwise Specified)

Parameter	Symbol	Value	Unit	Test Conditions	Notes
Repetitive Peak Reverse Voltage	$V_{RRM}$	1200	V		
DC Blocking Voltage	$V_{DC}$	1200			
Continuous Forward Current	$I_F$	54.5	A	$T_J = 25^\circ\text{C}$	Fig. 3
		26		$T_J = 135^\circ\text{C}$	
		20		$T_J = 150^\circ\text{C}$	
Repetitive Peak Forward Surge Current	$I_{FRM}$	91		$T_C = 25^\circ\text{C}, t_p = 10\text{ ms}, \text{Half Sine Wave}$	
		61		$T_C = 110^\circ\text{C}, t_p = 10\text{ ms}, \text{Half Sine Wave}$	
Power Dissipation	$P_{tot}$	250	W	$T_J = 25^\circ\text{C}$	Fig. 4
		112.5		$T_J = 110^\circ\text{C}$	
Diode dV/dt ruggedness	dV/dt	250	V/ns	$V_R = 0\text{-}960\text{V}$	
$i^2t$ value	$i^2t$	84.5	$\text{A}^2\text{s}$	$T_C = 25^\circ\text{C}, t_p = 10\text{ ms}$	
		60.5		$T_C = 110^\circ\text{C}, t_p = 10\text{ ms}$	

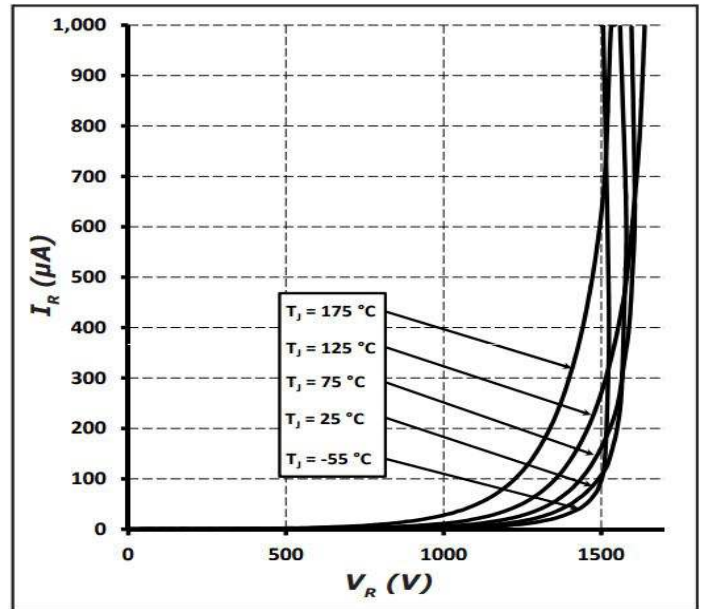
## Electrical Characteristics

Parameter	Symbol	Typ.	Max.	Unit	Test Conditions	Notes
Forward Voltage	$V_F$	1.5	1.8	V	$I_F = 20 \text{ A}, T_j = 25 \text{ }^\circ\text{C}$	Fig. 1
		2.2			$I_F = 20 \text{ A}, T_j = 175 \text{ }^\circ\text{C}$	
Reverse Current	$I_R$	35	200	$\mu\text{A}$	$V_R = 1200 \text{ V}, T_j = 25 \text{ }^\circ\text{C}$	Fig. 2
		65			$V_R = 1200 \text{ V}, T_j = 175 \text{ }^\circ\text{C}$	
Total Capacitive Charge	$Q_C$	99		nC	$V_R = 800 \text{ V}, T_j = 25 \text{ }^\circ\text{C}$	Fig. 5
Total Capacitance	C	1500		pF	$V_R = 0 \text{ V}, T_j = 25 \text{ }^\circ\text{C}, f = 1 \text{ MHz}$	

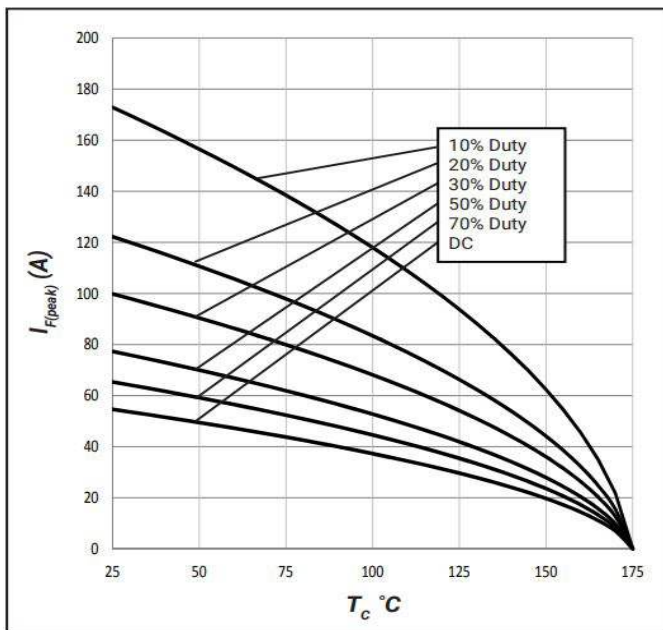
Typical Performance



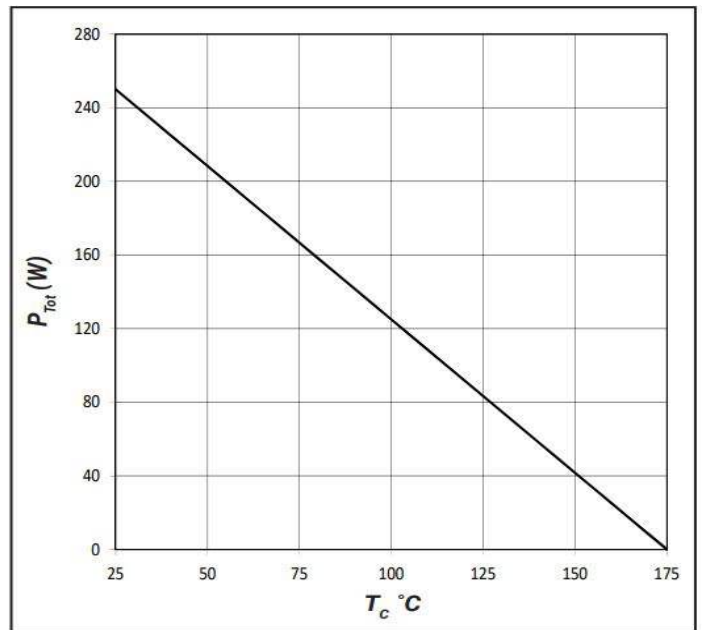
**Figure 1**  
Forward Characteristics



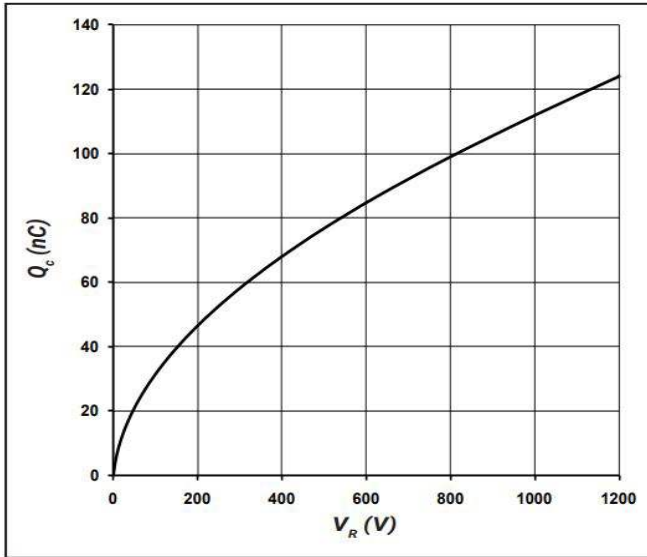
**Figure 2**  
Reverse Characteristics



**Figure 3**  
Current Derating

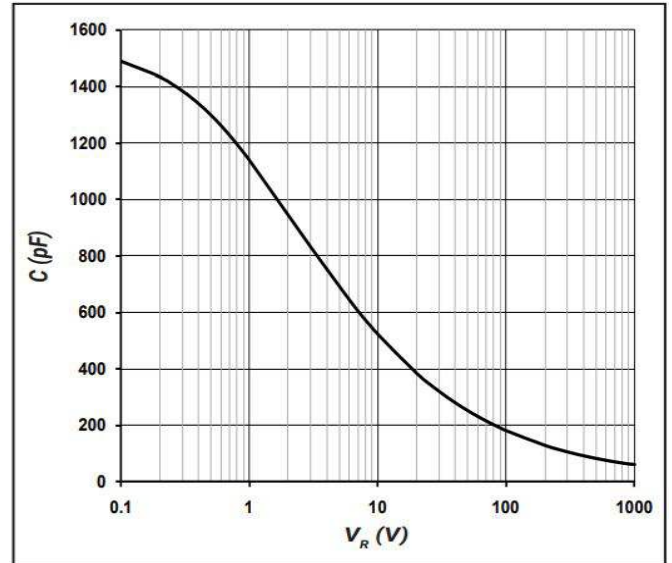


**Figure 4**  
Power Derating



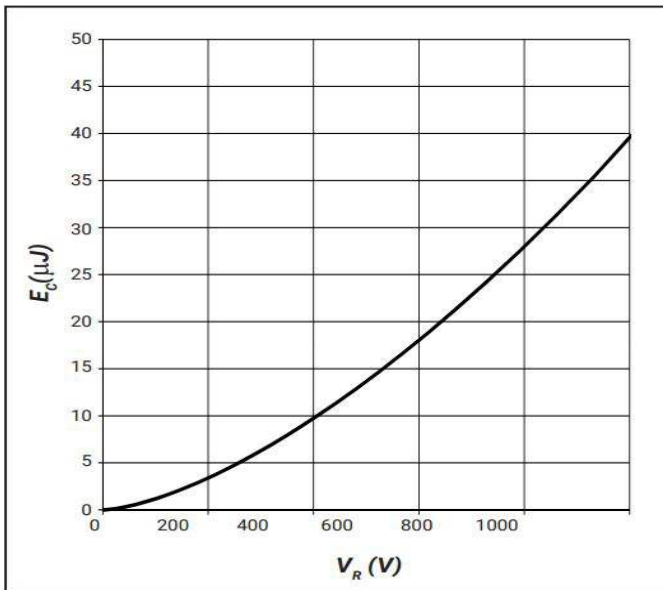
**Figure 5**

Total Capacitance vs. Reverse Voltage



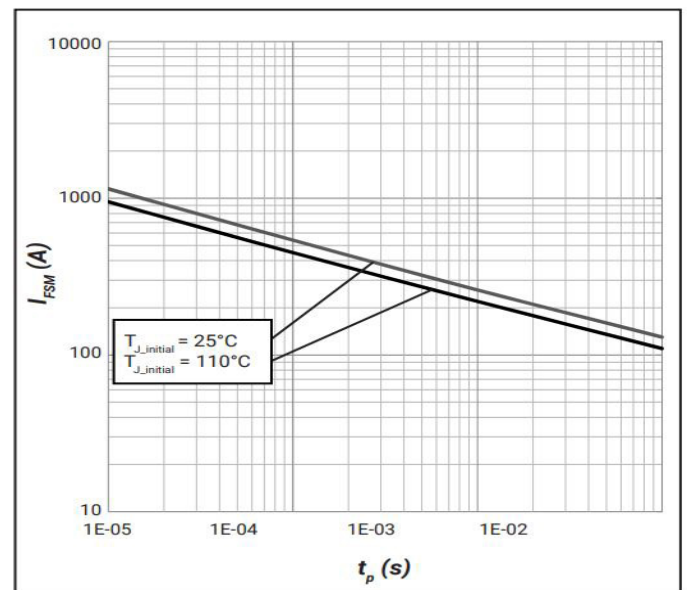
**Figure 6**

Capacitance vs. Reverse Voltage



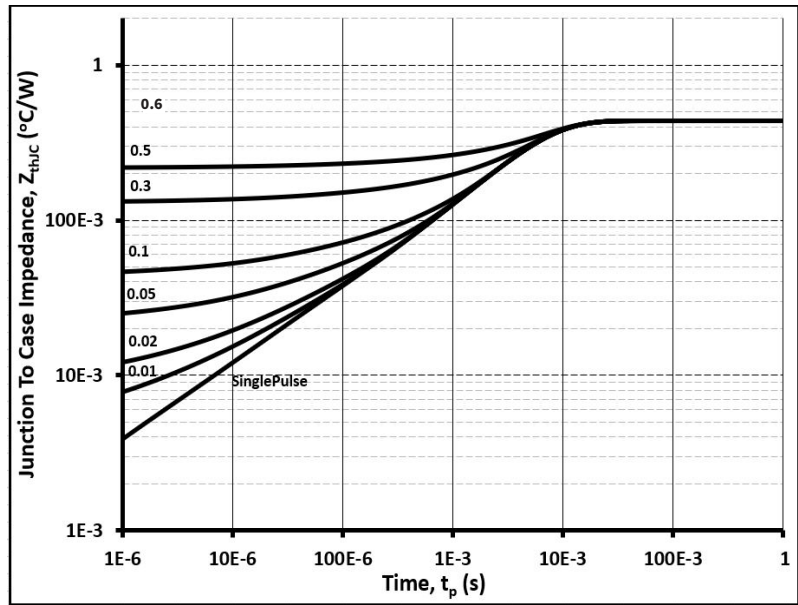
**Figure 7**

Capacitance Stored Energy



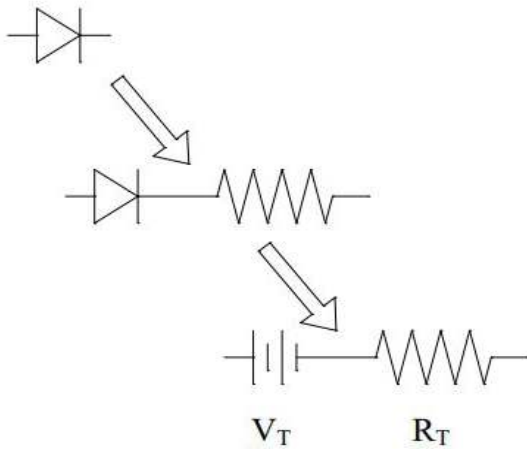
**Figure 8**

Non Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform)



**Figure 9**  
Transient Thermal Impedance

**Diode Model**



$$V_{IT} = V_T + I_f * R_T$$

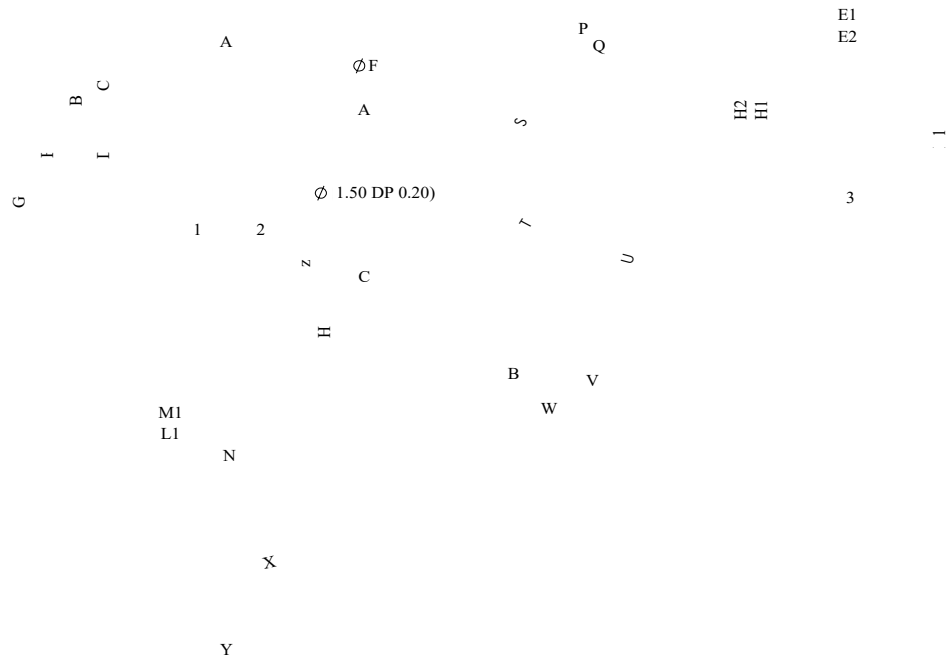
$$V_T = 0.97 + (T_J * -1.40 * 10^{-3})$$

$$R_T = 0.023 + (T_J * 2.71 * 10^{-4})$$

Note:  $T_J$  = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

## Package Dimensions & Pin-Out

Package: TO-220-2



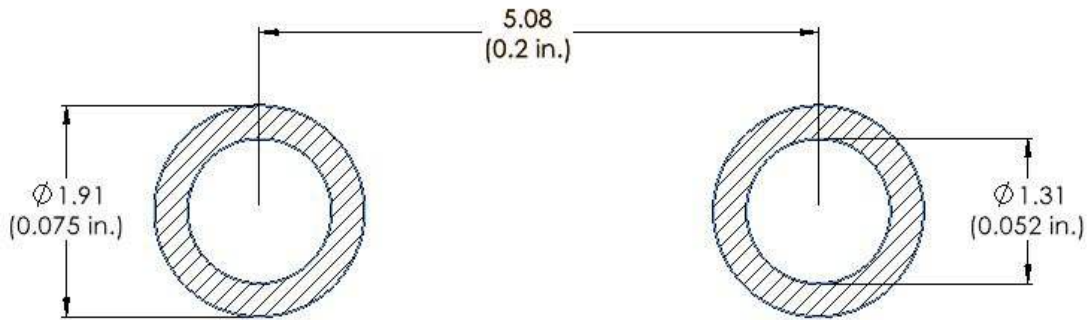
### NOTE

1. ALL METAL SURFACES ARE TIN PLATED (MATTE), EXCEPT AREA OF CUT.
2. DIMENSIONING & TOLERANCING CONFORM TO ASME Y14.5M-1994.
3. ALL DIMENSIONS ARE LISTED IN MILLIMETERS. ANGLES ARE IN DEGREES.
4. PACKAGE BURR FLASH SIZE (0.5 mm) IS NOT INCLUDED IN THE DIMENSIONS



### Recommended Solder Pad Layout

Primary dimensions shown in mm.



### Product Ordering Information

Order Number	Packing Type
E4D20120A	Tube



## Revision History

Document Version	Date of Release	Description of Changes
0	July-2018	Initial Release
1	April-2023	Update Package Drawing Update Landing Pad





## Notes & Disclaimer

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